



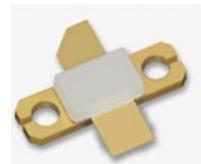
## GaN 28V 90W,C band RF Power Transistor

### Description

The YTAH58095GX is a 90W internally matched, GaN HEMT, designed from 5.0 to 6.0GHz, especially 5G NR or LTE application, as well as either Pulse or CW application

There is no guarantee of performance when this part is used in applications designed outside of these frequencies.

**YTAH58095GX**



- Typical performance (on fixture with device soldered)

$V_{DD}=28V$   $I_{DQ}=200mA$ , CW, 5.7-5.9GHz narrow band

Freq(MHz)	Pin(dBm)	Pout(dBm)	Pout(W)	IDS(A)	Gain(dB)	Eff(%)
5700	41.5	50	100.00	6.57	8.5	55
5800	41.08	50.1	102.33	6.62	9.0	55
5900	41.1	49.96	99.08	6.12	8.9	57

$V_{DD}=28V$   $I_{DQ}=200mA$ , CW, 5.1-5.3GHz narrow band

Freq(MHz)	Pin(dBm)	Pout(dBm)	Pout(W)	IDS(A)	Gain(dB)	Eff(%)
5100	41.7	50.27	106.41	6.48	8.57	58.65
5200	41.8	50.38	109.14	6.64	8.58	58.70
5300	41.8	50.22	105.20	6.4	8.42	58.70

Recommended driver: XTAH58020C6

### Applications and Features

- Suitable for wireless communication infrastructure, wideband amplifier, EMC testing, ISM etc.
- High Efficiency and Linear Gain Operations
- Thermally Enhanced Industry Standard Package
- High Reliability Metallization Process
- Excellent thermal Stability and Excellent Ruggedness
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

### Important Note: Proper Biasing Sequence for GaN HEMT Transistors

#### Turning the device ON

- Set VGS to the pinch-off (VP) voltage, typically  $-5V$
- Turn on VDS to nominal supply voltage (28V)
- Increase VGS until IDS current is attained
- Apply RF input power to desired level

#### Turning the device OFF

- Turn RF power off
- Reduce VGS down to VP, typically  $-5V$
- Reduce VDS down to  $0V$
- Turn off VGS

**Table 1. Maximum Ratings**

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	150	Vdc
Gate-Source Voltage	$V_{GS}$	-10,+2	Vdc
Operating Voltage	$V_{DD}$	36	Vdc
Maximum Forward Gate Current @ $T_c = 25^\circ C$	$I_{Gmax}$	24	mA
Storage Temperature Range	$T_{Stg}$	-65 to +150	°C
Case Operating Temperature	$T_c$	+150	°C
Operating Junction Temperature(See note 1)	$T_j$	+225	°C
Total Device Power Dissipation (Derated above $25^\circ C$ , see note 2)	$P_{diss}$	125	W

Note: 1. Continuous operation at maximum junction temperature will affect MTTF

2. Bias Conditions should also satisfy the following expression:  $Pdiss < (Tj - Tc) / RJC$  and  $Tc = Tcase$

**Table 2. Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case $T_C = 85^\circ\text{C}$ , $T_J = 200^\circ\text{C}$ , RF CW operation	$R_{\theta JC}$	1.6	C/W

**Table 3. Electrical Characteristics (T<sub>C</sub> = 25°C unless otherwise noted)**

## DC Characteristics

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS}=-8V$ ; $I_{DS}=24mA$	$V_{DSS}$	150			V
Gate Threshold Voltage	$V_{DS} = 28V$ , $I_D = 24mA$	$V_{GS(th)}$	-4		-2	V
Gate Quiescent Voltage	$V_{DS} = 28V$ , $I_{DS}=200mA$ , Measured in Functional Test	$V_{GS(Q)}$		-2.8		V

## Typical performance

5.7-5.9GHz

**Figure 2: Small singal gain and return loss Vs Frequency**

**Vds=28V, Idq=200mA, input power=0dBm**

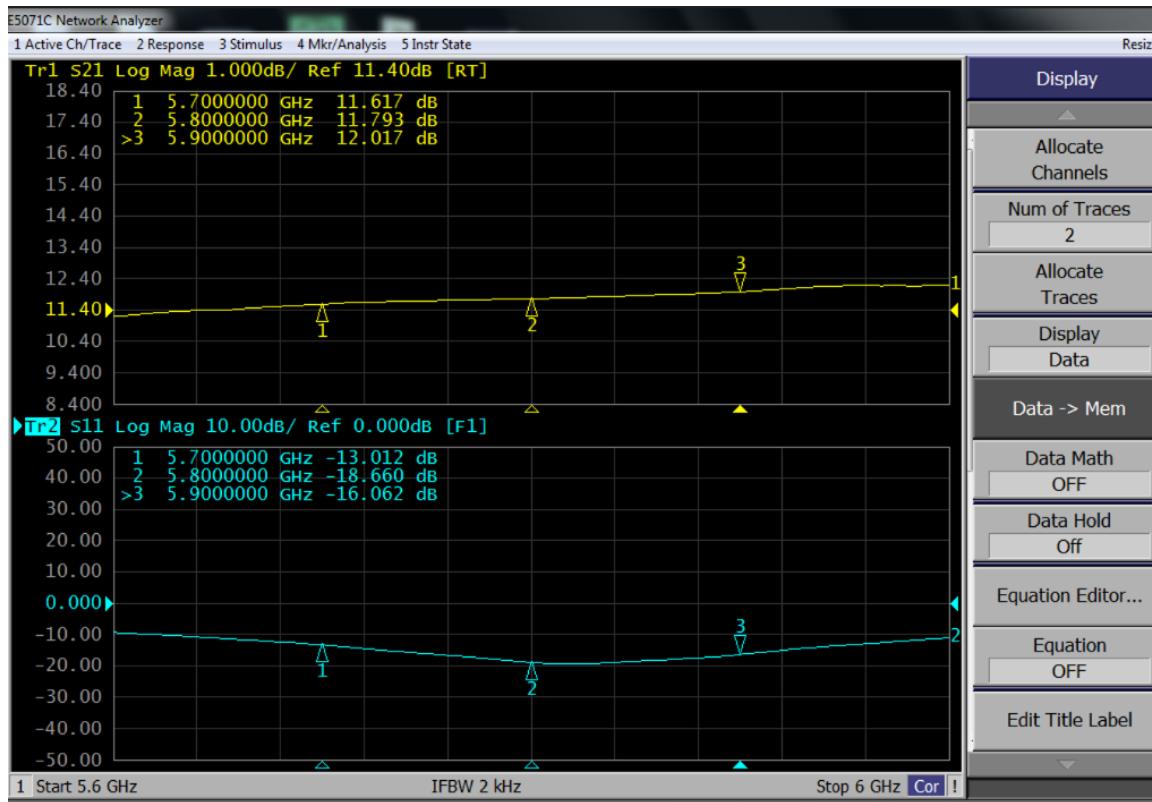
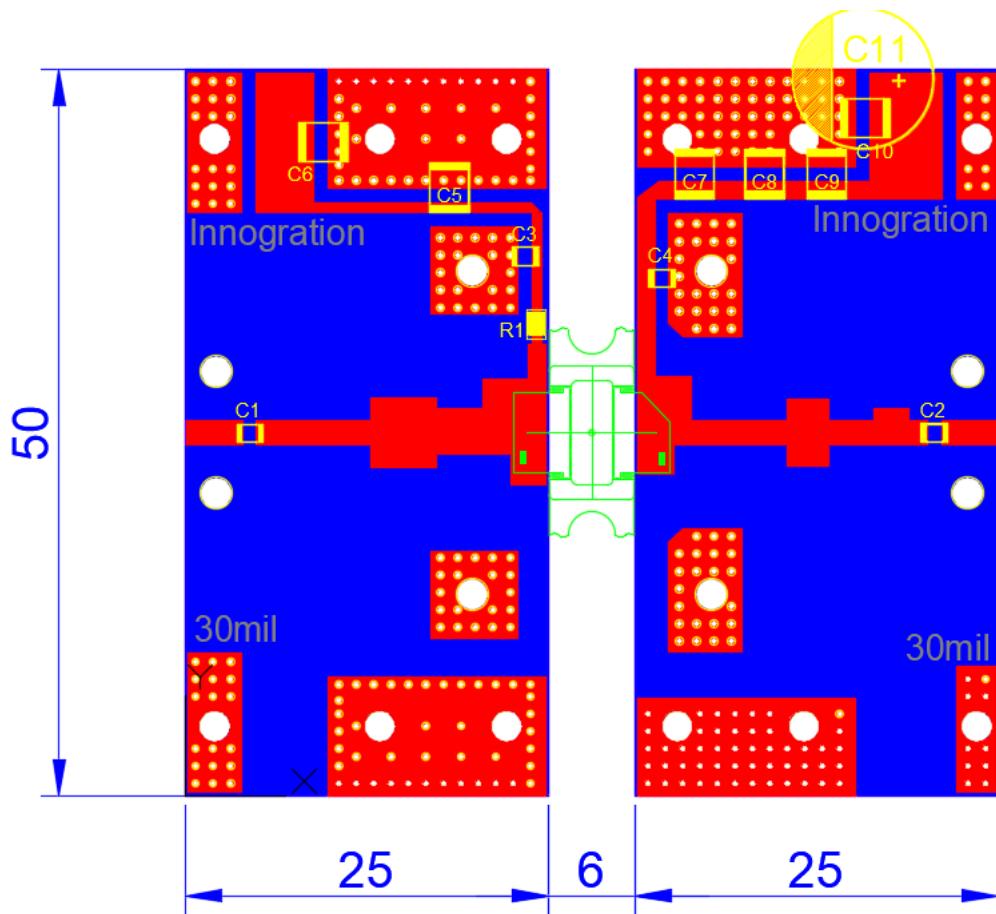


Figure 4: Picture and Bill of materials of application circuit  
(Layout Gerber file upon request, 20mils RO4350B)



Component	Description	Suggested Manufacturer
C11	470uF/63V	
C5-C10	10uF(1210)	-
C1-C4	3.9pF(MQ300805)	-
R1	Chip Resistor,10Ω, (0805)	
PCB	Rogers 4350B, Er = 3.48, thickness 30 mils, 1oz copper	

## Typical performance

### 5.1-5.3GHz

Figure 5: Small singal gain and return loss Vs Frequency

Vds=28V, Idq=200mA, input power=0dBm

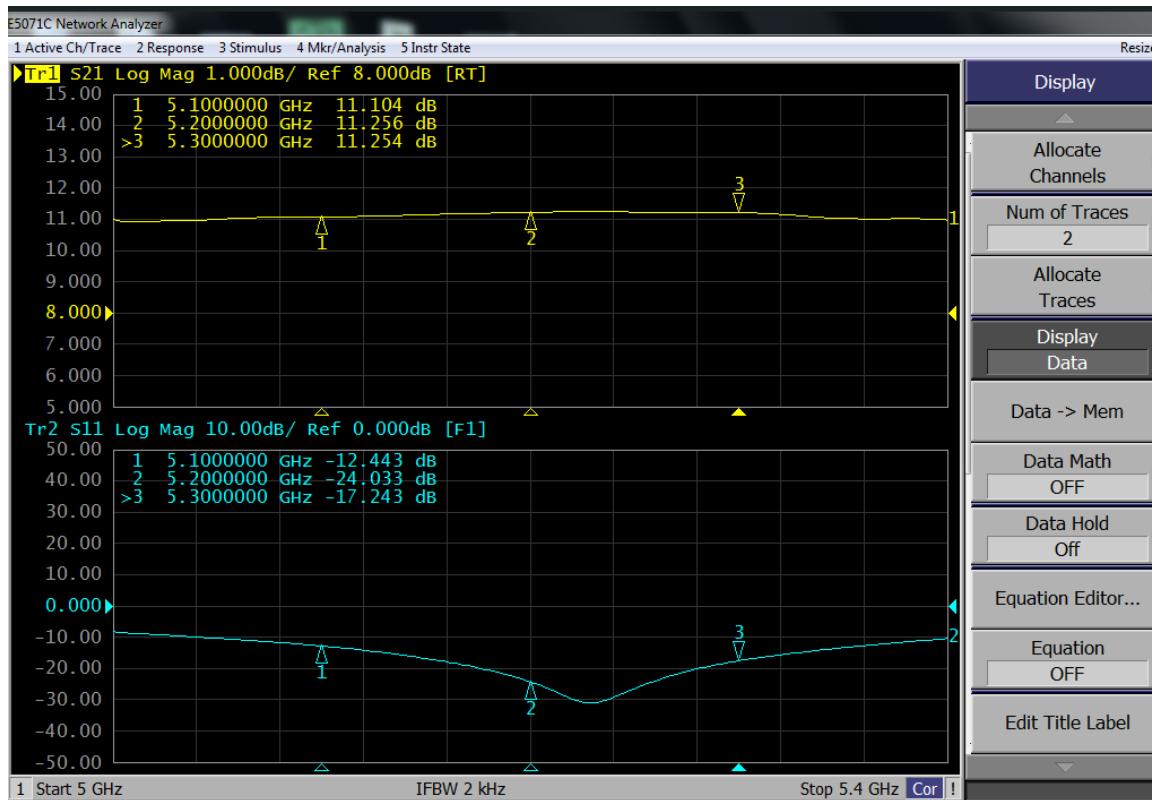
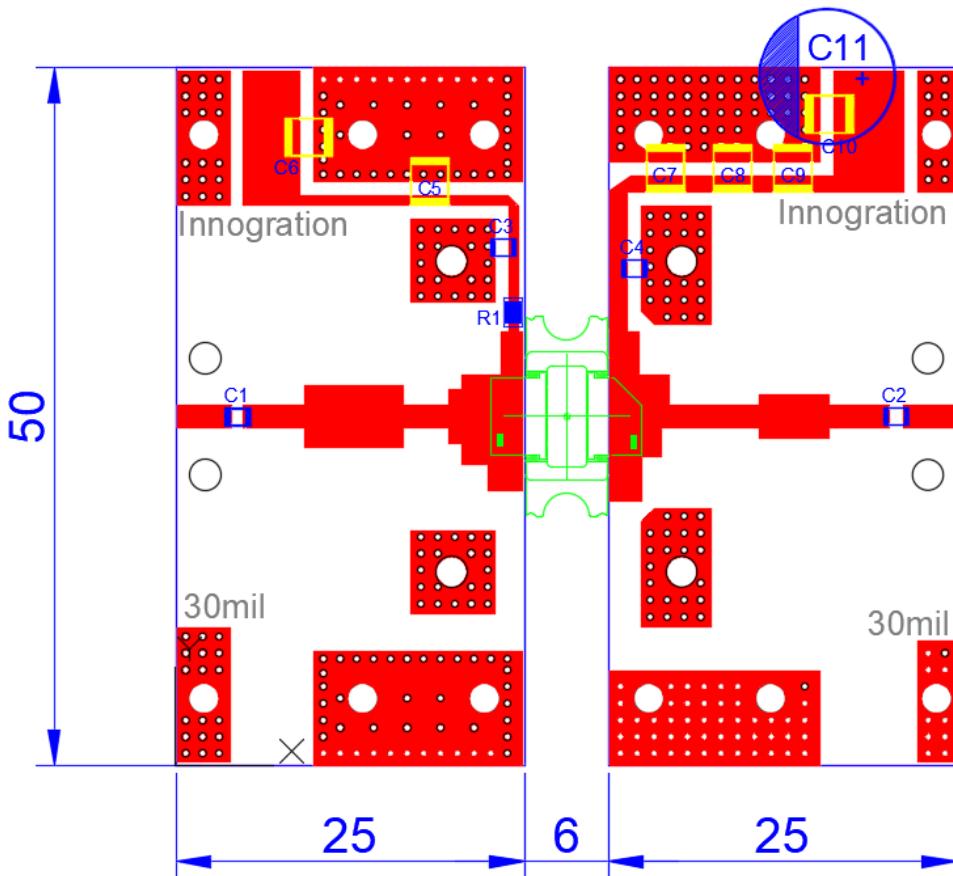


Figure 6: Picture and Bill of materials of application circuit  
(Layout Gerber file upon request, 20mils RO4350B)



Component	Description	Suggested Manufacturer
C11	470uF/63V	
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PCB	Rogers 4350B, Er = 3.48, thickness 30 mils, 1oz copper	



## Flanged ceramic package; 2 leads

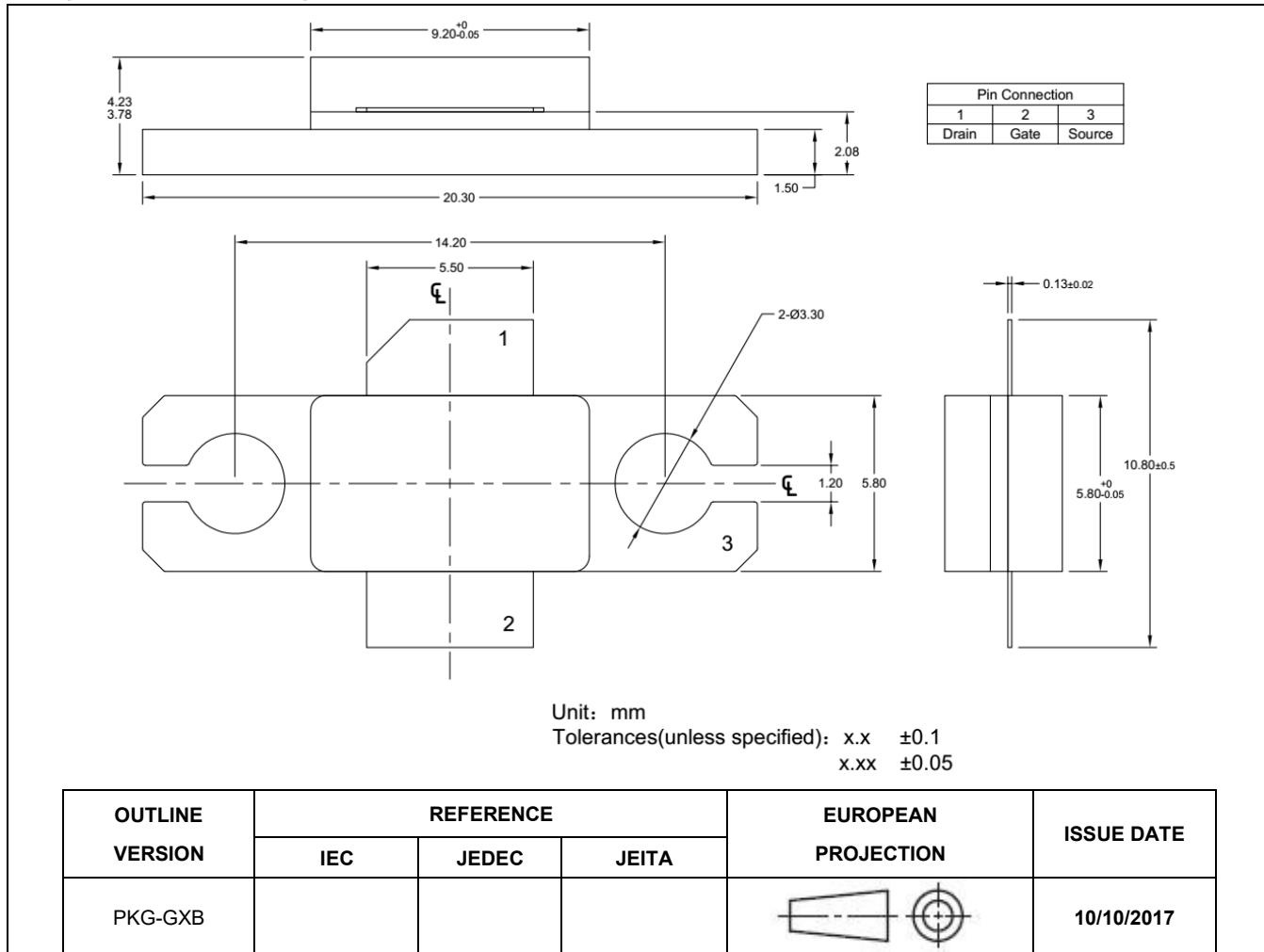


Figure 1. Package Outline PKG-G2E

## Revision history

Table 5. Document revision history

Date	Revision	Datasheet Status
2026/1/22	V1.0	Preliminary Datasheet Creation

Application data based on YHG-26-04/05

## Notice

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